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Vishay Siliconix

Automotive P-Channel 150 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY				
V _{DS} (V)	-150			
$R_{DS(on)}(\Omega)$ at $V_{GS} = -10 \text{ V}$	1.77			
I _D (A)	-0.84			
Configuration	Single			

SOT-23 (TO-236) G P-Channel MOSFET

FEATURES

- TrenchFET® power MOSFET
- AEC-Q101 qualified
- 100 % R_q and UIS tested
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912





ROHS COMPLIANT HALOGEN FREE

Marking Code: 8Rxxx

ORDERING INFORMATION	
Package	SOT-23
Lead (Pb)-free and Halogen-free	SQ2325ES-T1-GE3

ABSOLUTE MAXIMUMRATINGS (T _C = 25 °C, unless otherwise noted)					
PARAMETER	SYMBOL	LIMIT	UNIT		
Drain-Source Voltage	V_{DS}	-150	V		
Gate-Source Voltage	V_{GS}	± 20	V		
Continuous Drain Current	T _C = 25 °C	-	-0.84		
Continuous Drain Current	T _C = 125 °C	I _D	-0.48		
Continuous Source Current (Diode Conductio	I _S	-3.7	Α		
Pulsed Drain Current ^a	I _{DM}	-2			
Single Pulse Avalanche Current	L = 0.1 mH	I _{AS}	4.8		
Single Pulse Avalanche Energy	L = 0.1 IIII	E _{AS}	1.12	mJ	
Mayimum Dayar Dissination 8	T _C = 25 °C	D	3	W	
Maximum Power Dissipation ^a	T _C = 125 °C	P_{D}	1	VV	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	-55 to +175	°C	

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	LIMIT	UNIT	
Junction-to-Ambient	PCB Mount b	R _{thJA}	166	°C/W	
Junction-to-Foot (Drain)		R _{th.IF}	50	C/VV	

Notes

- a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$
- b. When mounted on 1" square PCB (FR4 material).



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PARAMETER	SYMBOL	TES	MIN.	TYP.	MAX.	UNIT	
Static							
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 \text{ V}, I_D = -250 \mu\text{A}$		-150	-	-	V
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} =	$V_{DS} = V_{GS}, I_D = -250 \mu A$		-3	-3.5	V
Gate-Source Leakage	I _{GSS}	V _{DS} =	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$		-	± 100	nA
		V _{GS} = 0 V	V _{DS} = -150 V	-	-	-1	
Zero Gate Voltage Drain Current	I _{DSS}	$V_{GS} = 0 V$	V _{DS} = -150 V, T _J = 125 °C	-	-	-50	μΑ
		V _{GS} = 0 V	V _{DS} = -150 V, T _J = 175 °C	-	-	-150	
On-State Drain Current ^a	I _{D(on)}	V _{GS} = -10 V	$V_{DS} \ge 5 V$	-0.8	-	-	Α
		V _{GS} = -10 V	I _D = -0.5 A	-	1.3	1.77	Ω
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = -10 V	I _D = -0.5 A, T _J = 125 °C	-	-	3.4	
		V _{GS} = -10 V	I _D = -0.5 A, T _J = 175 °C	-	-	4.4	
Forward Transconductance b	9fs	V _{DS} = -15 V, I _D = -0.5 A		-	2.2	-	S
Dynamic ^b	•	•					
Input Capacitance	C _{iss}			-	200	250	
Output Capacitance	C _{oss}	$V_{GS} = 0 V$	V _{DS} = -50 V, f = 1 MHz	-	20	25	pF
Reverse Transfer Capacitance	C _{rss}]		-	17	22	
Total Gate Charge ^c	Qg			-	7.4	10	
Gate-Source Charge ^c	Q _{gs}	V _{GS} = -10 V	$V_{DS} = -75 \text{ V}, I_D = -0.5 \text{ A}$	-	1.1	-	nC
Gate-Drain Charge ^c	Q _{gd}	1		-	2.9	-	
Gate Resistance	R _g	f = 1 MHz		2.8	3.9	6.1	Ω
Turn-On Delay Time ^c	t _{d(on)}				8	12	
Rise Time ^c	t _r	V_{DD} = -75 V, R_L = 150 Ω I_D \cong -0.5 A, V_{GEN} = -10 V, R_g = 1 Ω		-	14	18	- ns
Turn-Off Delay Time ^c	t _{d(off)}			-	15	20	
Fall Time ^c	t _f			-	10	14	
Source-Drain Diode Ratings and Chara	acteristics ^b						
Pulsed Current ^a	I _{SM}			-	-	-2	Α
Forward Voltage	V _{SD}	$I_F = -0.5 \text{ A}, V_{GS} = 0 \text{ V}$			-0.8	-1.2	V

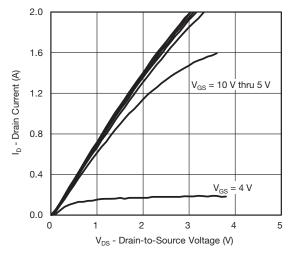
Notes

- a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

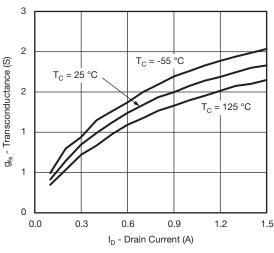
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



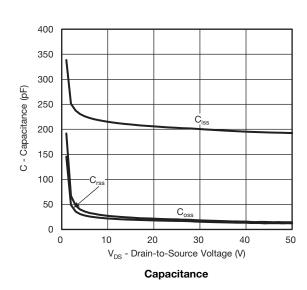
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)

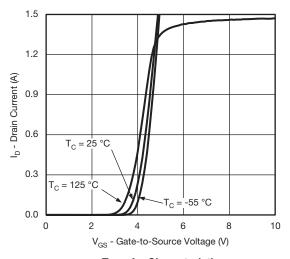


Output Characteristics

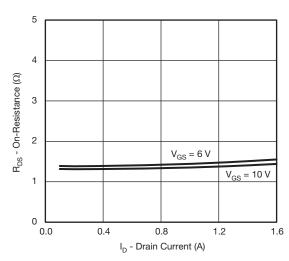


Transconductance

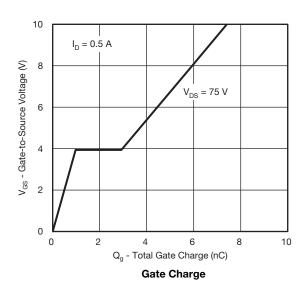




Transfer Characteristics

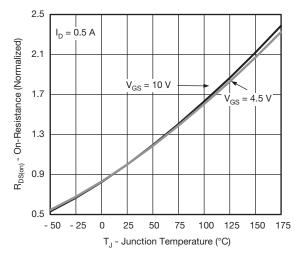


On-Resistance vs. Drain Current

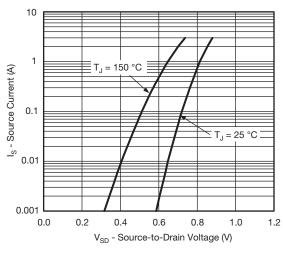




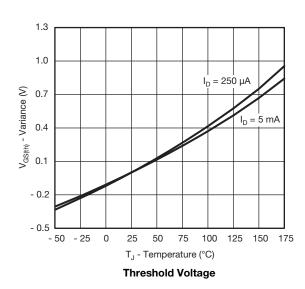
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)

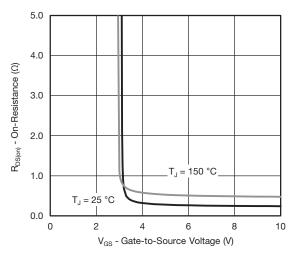


On-Resistance vs. Junction Temperature

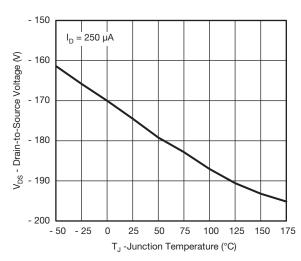


Source-Drain Diode Forward Voltage

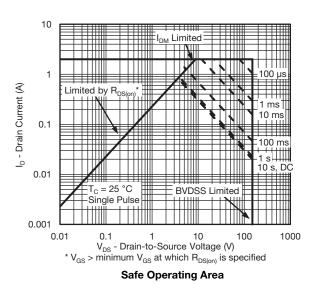




On-Resistance vs. Gate-to-Source Voltage

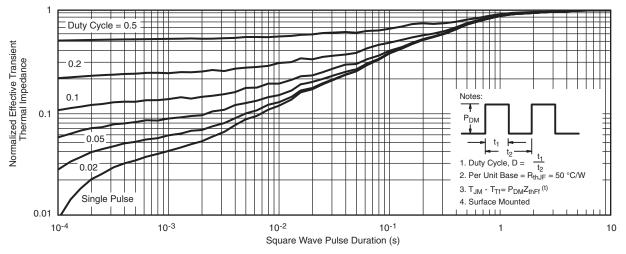


Drain Source Breakdown vs. Junction Temperature

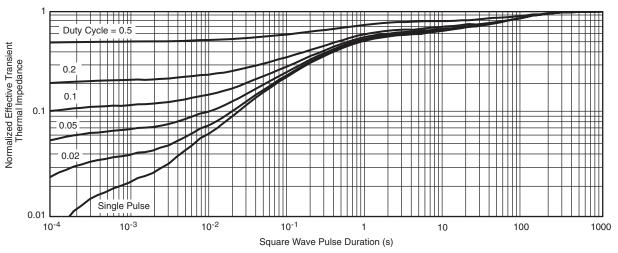




THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Foot



Normalized Thermal Transient Impedance, Junction-to-Ambient

Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
 - Normalized Transient Thermal Impedance Junction-to-Foot (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg267847.





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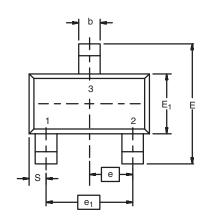
REVISION HISTORY ^a				
REVISION	REVISION DATE DESCRIPTION OF CHANGE			
В	30-Jan-15	Redesigned to meet AEC-Q101 rev D.		

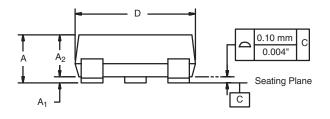
Note

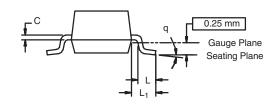
a. As of April 2014

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SOT-23 (TO-236): 3-LEAD







Dim	MILLI	METERS	INCHES		
	Min	Max	Min	Max	
Α	0.89	1.12	0.035	0.044	
A ₁	0.01	0.10	0.0004	0.004	
A ₂	0.88	1.02	0.0346	0.040	
b	0.35	0.50	0.014	0.020	
С	0.085	0.18	0.003	0.007	
D	2.80	3.04	0.110	0.120	
Е	2.10	2.64	0.083	0.104	
E ₁	1.20	1.40	0.047	0.055	
е	0.95 BSC		0.0374 Ref		
e ₁	1.9	0 BSC	0.074	8 Ref	
L	0.40	0.60	0.016	0.024	
L ₁	0.64 Ref		0.025 Ref		
S	0.50 Ref		0.020 Ref		
q	3°	8°	3°	8°	
FCN: S-03946-Rev K 09-	lul-01				

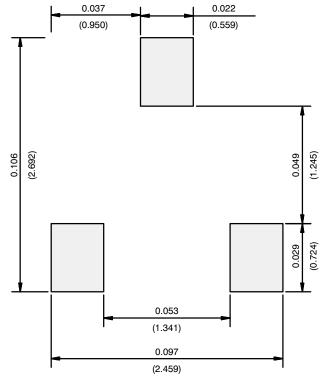
ECN: S-03946-Rev. K, 09-Jul-01

DWG: 5479

Document Number: 71196 www.vishay.com 09-Jul-01



RECOMMENDED MINIMUM PADS FOR SOT-23



Recommended Minimum Pads Dimensions in Inches/(mm)

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APPLICATION NOTE



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